

PEMH20; PUMH20

NPN/NPN resistor-equipped transistors;

R1 = 2.2 k Ω , R2 = 2.2 k Ω

Rev. 04 — 15 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN resistor-equipped transistors.

Table 1. Product overview

Type number	Package		NPN/PNP complement	PNP/PNP complement
	NXP	JEITA		
PEMH20	SOT666	-	PEMD20	PEMB20
PUMH20	SOT363	SC-88	PUMD20	PUMB20

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		0.8	1	1.2	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1	<p>001aab555</p>	<p>sym063</p>
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMH20	-	plastic surface mounted package; 6 leads	SOT666
PUMH20	SC-88	plastic surface mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMH20	6K
PUMH20	H7*

[1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per transistor						
V _{CB0}	collector-base voltage	open emitter	-	50	V	
V _{CEO}	collector-emitter voltage	open base	-	50	V	
V _{EBO}	emitter-base voltage	open collector	-	10	V	
V _I	input voltage					
	positive		-	+12	V	
	negative		-	-10	V	
I _O	output current (DC)		-	100	mA	
I _{CM}	peak collector current		-	100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
T _{stg}	storage temperature		-65	+150	°C	
T _j	junction temperature		-	150	°C	
T _{amb}	ambient temperature		-65	+150	°C	
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT363		[1]	-	300	mW
	SOT666		[1][2]	-	300	mW

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	625	K/W
	SOT666		[1][2]	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	416	K/W
	SOT666		[1][2]	-	416	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

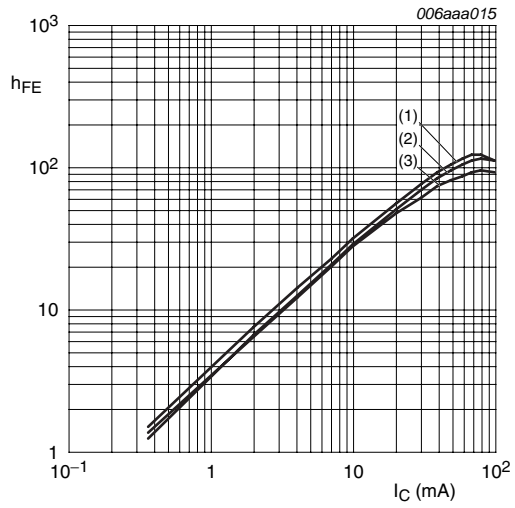
[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

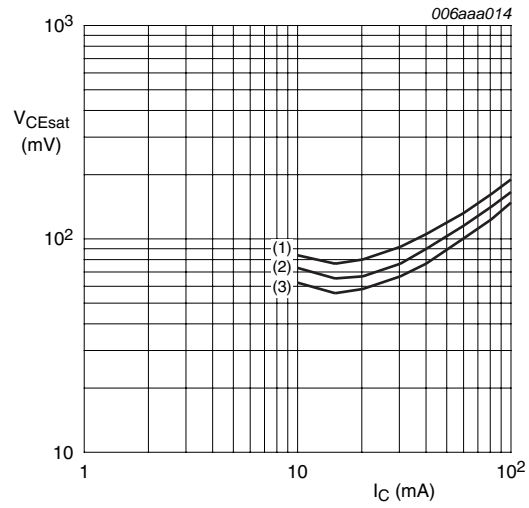
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
I_{CBO}	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	μA
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	2	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 20\text{ mA}$	30	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	-	1.2	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}; I_C = 20\text{ mA}$	2	1.6	-	V
R1	bias resistor1 (input)		1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		0.8	1	1.2	
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	2.5	pF



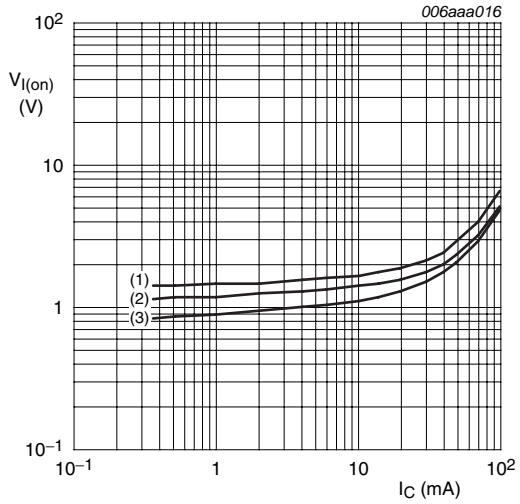
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig. 1. DC current gain as a function of collector current; typical values



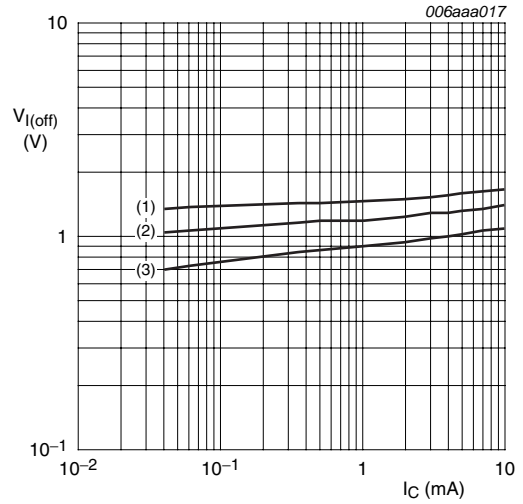
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig. 2. Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3\text{ V}$
 (1) $T_{amb} = -40\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

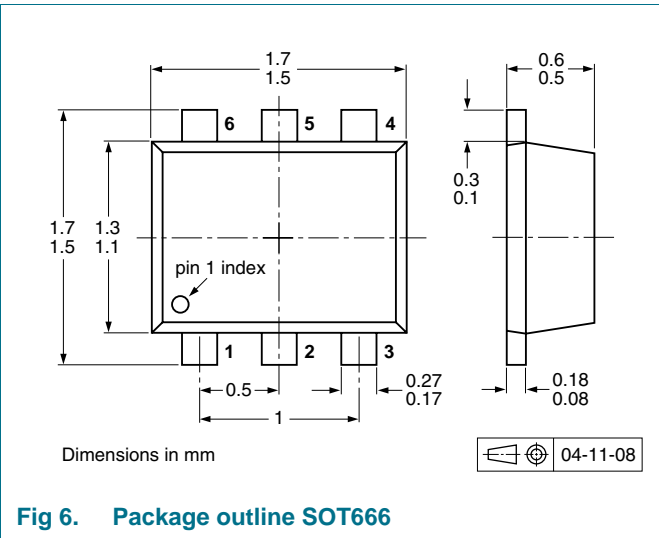
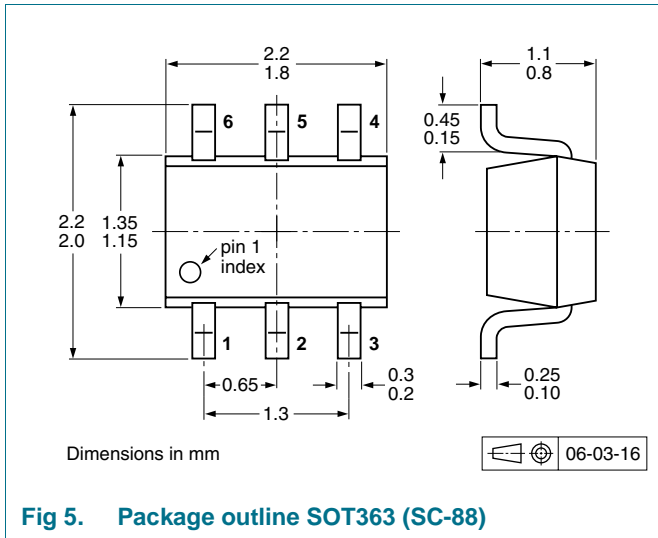
Fig. 3. On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -40\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 4. Off-state input voltage as a function of collector current; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMH20	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH20	SOT363	4 mm pitch, 8 mm tape and reel; T1	^[2] -115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	^[3] -125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 12](#).

[2] T1: normal taping

[3] T2: reverse taping

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH20_PUMH20_4	20091115	Product data sheet	-	PEMH20_PUMH20_3
Modifications:	<ul style="list-style-type: none"> This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 5 "Package outline SOT363 (SC-88)"; updated 			
PEMH20_PUMH20_3	20050214	Product data sheet	-	PUMH20_2
PUMH20_2	20040414	Product specification	-	PUMH20_1
PUMH20_1	20031016	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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